## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: **TAUBER et. al** Application Serial No.: **10/785,510** Application Filed: **February 17, 2004** Attorney Docket No.: **CECOM 5522** 

For: RARE EARTH METAL COMPOUNDS FOR USE IN HIGH CRITICAL

TEMPERATURE THIN FILM SUPER-CONDUCTING ANTENNAS

## **AMENDMENTS TO THE CLAIMS**

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In accordance with the enclosed Remarks, please amend the claims in the above-identified application as follows:

1-47 (Canceled)

48. (Previously Presented) An-A high  $T_c$  superconducting antenna, comprising:

a single layer of a copper oxide superconductor deposited onto a single crystal substrate of the formula Sr<sub>2</sub>LuSbO<sub>6</sub>;

said single crystal substrate being heated for at least 20 hours at between 1400° C and 1600° C;

said single crystal substrate being constructed in a bulk form;

said single crystal substrate having an ordered perovskite cubic crystalline structure;

said single crystal substrate having a low dielectric constant of 15.1;

said single crystal substrate having a low dielectric loss of less than  $1 \times 10^{-3}$  without a phase transition;

said formula including an  $\mathrm{Sb}^{5+}$  constituent atom with a polarizability of about 1.2 Å<sup>3</sup>; and said single layer of the copper oxide superconductor being patterned to complete the

30 device.

## 49-79 (Canceled)

80. (Previously Presented) A high T<sub>c</sub> superconductingAn antenna device, comprising: a single layer of a copper oxide superconductor deposited onto a substrate; said substrate having a buffered layer with the formula Sr<sub>2</sub>LuSbO<sub>6</sub>; said buffered layer being heated for at least 20 hours at between 1400° C and 1600° C; said buffered layer having an ordered perovskite cubic crystalline structure; said buffered layer having a low dielectric constant of 15.1; said buffered layer having a low dielectric loss of less than 1 x 10<sup>-3</sup> without a phase

10 transition;

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said formula including an  $\mathrm{Sb}^{5+}$  constituent atom with a polarizability of about 1.2 Å<sup>3</sup>; and said single layer of the copper oxide superconductor being patterned to complete the device.